SILICON PNP TRANSISTOR
EPITAXIAL PLANAR TYPE (PCT PROCESS)

KTA 817A

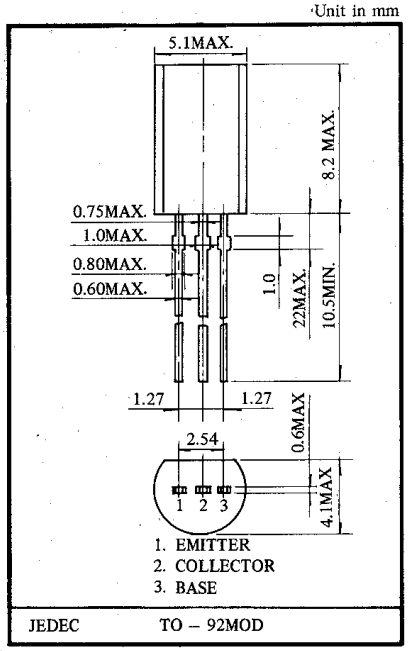
APPLICATIONS

- Driver Stage Amplifier Applications.
- Voltage Amplifier Applications.

FEATURES

- Complementary to KTC 1627 A.
- Driver Stage Application of 30 to 35 Watts Amplifiers.

Unit in mm



■ MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	−80	V
Collector-Emitter Voltage	V_{CEO}	−80	V
Emitter-Base Voltage	V_{EBO}	−5	V
Collector Current	I_C	−400	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Emitter Current	I_E	400	mA
Collector Dissipation	P_C	800	mW
Junction Temperature	T_j	150	℃
Storage Temperature	Tstg	-55~150	℃

■ ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cutoff Current	I_{CBO}	V_{CB}=−50 V, I_E=0	−	−	−100	nA
Emitter Cutoff Current	I_{EBO}	V_{EB}=−5 V, I_C=0	−	−	−100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=−5 mA	−80	−	−	V
DC Current Gain	$h_{FE(1)}$	V_{CE}=−2 V, I_C=−50 mA	70	−	240	
	$h_{FE(2)}$	V_{CE}=−2 V, I_C=−200 mA	40	−	−	
Collector-Emitter Saturation Voltage	$V_{CE(Sat)}$	I_C=−200 mA, I_B=−20 mA	−	−	−0.4	V
Base-Emitter Voltage	V_{BE}	V_{CE}=−2 V, I_C=−5 mA	−0.55	−	−0.8	V
Transition Frequency	f_T	V_{CE}=−10 V, I_C=−10 mA	−	100	−	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=−10 V, I_E=0, f=1 MHz	−	14	−	pF

■ NOTE: According to h_{FE}(1), Classified as follows.

O	70−140	Y	120−240

KEC